

CLAIMS

What is claimed is:

1. A skin-texture sensor for sensing a skin texture having a plurality of ridges and a plurality of valleys, comprising:
 - a) a base;
 - b) a plurality of conductive row lines disposed on the base;
 - c) a plurality of conductive column lines disposed on the base and insulated from the row lines; and
 - d) an array of membrane switches disposed on the base such that a spacing between adjacent switches in the array is less than one half of a spacing between adjacent ridges, each membrane switch corresponding to a pair of one of the row lines and one of the column lines, said each membrane switch comprising:
 - a lower electrode disposed on the base and electrically connected to said one of the row lines, and
 - a flexible upper membrane structure disposed over and spaced apart from the lower electrode when in a quiescent state, the membrane structure comprising an upper electrode disposed facing the lower electrode and connected to said one of the column lines, whereinapplying a ridge of the texture to said each membrane switch causes a flexure of the membrane resulting in a contact between the lower electrode and the upper electrode, the contact establishing an electrical communication between said one of the row

lines and said one of the column lines, and
wherein

disposing a valley of the texture over said each
membrane switch does not result in the
contact between the lower electrode and the
upper electrode.

2. The sensor of claim 1 wherein the upper electrode
comprises a conductive membrane anchored to the base
around an edge of the conductive membrane.

3. The sensor of claim 2, wherein the membrane structure
further comprises an insulative diaphragm stacked over
the upper electrode and anchored to the base around an
edge of the insulative diaphragm.

4. The sensor of claim 3, wherein a height of a top
surface of the insulative diaphragm is within 4 μm
of a top height of a support surface of the sensor,
the support surface being outside of any membrane
structure of the array.

5. The sensor of claim 4, wherein the height of the
top surface is within 0.5 μm of the top height of
the support surface.

6. The sensor of claim 3, wherein the insulative
diaphragm is formed by a polymer layer.

7. The sensor of claim 1, wherein the upper electrode
comprises a conductive membrane having an annular crease.

- 1 8. The sensor of claim 1, wherein the upper electrode
2 comprises a conductive membrane having at least two
3 concentric annular creases.
4
- 1 9. The sensor of claim 1, wherein said each membrane switch
2 defines a closed chamber defined generally between the
3 lower electrode and the membrane structure, the chamber
4 being closed to external particles so as to protect the
5 lower electrode and the upper electrode from
6 contamination.
7
- 1 10. The sensor of claim 9, wherein the closed chamber is
2 open to a passage of air from an external environment
3 of the sensor, for allowing an equalization of pressure
4 between the external environment and the closed
5 chamber.
6
- 1 11. The sensor of claim 9, wherein said each membrane
2 switch includes a set of sealed vents extending between
3 the chamber and an exterior of the chamber, wherein the
4 set of vents in an unsealed state provide access to the
5 chamber for removing a sacrificial material from the
6 chamber during a manufacture of the sensor.
7
- 1 12. The sensor of claim 9, further comprising a set of
2 interswitch tunnels establishing fluidic communication
3 between a plurality of closed chambers of adjacent
4 switches, for allowing an equalization of pressure
5 between the plurality of closed chambers.
6
- 1 13. The sensor of claim 1, further comprising a flexible
2 insulative sheet disposed over the array of membrane

switches, for coupling the texture to the membrane switches.

14. The sensor of claim 1, further comprising a passive resistor connected in series between said each membrane switch and a line selected from the pair of said one of the row lines and said one of the column lines.

15. The sensor of claim 14, further comprising a pull-down passive resistor connecting a line selected from each of the row lines and each of the column lines to a lower electrical potential, for improving a discrimination of the sensor between an open state and a closed state of said each membrane switch.

16. The sensor of claim 1, further comprising an active device connecting said each membrane switch and a line selected from the pair of said one of the row lines and said one of the column lines.

17. The sensor of claim 16, further comprising an active device connecting a line selected from each of the row lines and each of the column lines to a lower electrical potential.

18. The sensor of claim 1, wherein the base comprises a semiconductor substrate.

19. The sensor of claim 18, wherein the base further comprises an insulator layer disposed over the semiconductor substrate.

1 20. The sensor of claim 1, wherein the base comprises an
2 insulating substrate.

1 21. The sensor of claim 1, wherein the base comprises a glass
2 substrate.

1 22. The sensor of claim 1, wherein the skin texture is a
2 fingerprint texture, and said sensor is sized to sense a
3 fingerprint.

1 23. A skin-texture sensor for sensing a skin texture having a
2 plurality of ridges and a plurality of valleys, the sensor
3 comprising:

4 an array of membrane switches disposed on a base such that a
5 spacing between adjacent switches in the array is less
6 than one half of a spacing between adjacent ridges,
7 each membrane switch comprising:

- 8 a) a lower electrode disposed on the base; and
9 b) a flexible upper membrane structure disposed over the
10 lower electrode and comprising an upper electrode
11 disposed facing the lower electrode, wherein applying a
12 ridge of the texture to said each membrane switch
13 causes a flexure of the membrane resulting in a contact
14 between the lower electrode and the upper electrode,
15 and wherein disposing a valley of the texture over said
16 each membrane switch does not result in the contact
17 between the lower electrode and the upper electrode.

1 24. The sensor of claim 23 wherein the upper electrode
2 comprises a conductive membrane anchored to the base
3 around an edge of the conductive membrane.

1 25. The sensor of claim 24, wherein the membrane structure
2 further comprising an insulative diaphragm stacked over
3 the upper electrode and anchored to the base around an
4 edge of the insulative diaphragm.

5
1 26. The sensor of claim 23, wherein the upper electrode
2 comprises a conductive membrane having an annular crease.

3
1 27. The sensor of claim 23, wherein said each membrane switch
2 defines a closed chamber defined generally between the
3 lower electrode and the membrane structure, the chamber
4 being substantially closed to external particles so as to
5 protect the lower electrode and the upper electrode from
6 contamination.

7
1 28. The sensor of claim 27, wherein the closed chamber is
2 open to a passage of air from an external environment
3 of the sensor, for allowing an equalization of pressure
4 between the external environment and the closed
5 chamber.

6
1 29. The sensor of claim 27, further comprising a set of
2 interswitch tunnels establishing fluidic communication
3 between a plurality of closed chambers of adjacent
4 switches, for allowing an equalization of pressure
5 between the plurality of closed chambers.

6
1 30. A texture sensor for sensing a texture having a plurality of
2 protrusions and a plurality of valleys, the sensor
3 comprising:

4 an array of membrane switches disposed on a base, each
5 membrane switch comprising:

6 a) a lower electrode disposed on the base; and

7 b) a flexible upper membrane structure disposed over the
8 lower electrode and spaced apart from the lower
9 electrode when in a quiescent state, the upper membrane
10 structure comprising an upper electrode disposed facing
11 the lower electrode, wherein disposing a protrusion of
12 the texture over said each membrane switch causes a
13 flexure of the membrane resulting in a contact between
14 the lower electrode and the upper electrode, and
15 wherein disposing a valley of the texture over said
16 each membrane switch does not result in the contact
17 between the lower electrode and the upper electrode.

18
1 31. The sensor of claim 30 wherein the upper electrode
2 comprises a conductive membrane anchored to the base
3 around an edge of the conductive membrane.

4
1 32. The sensor of claim 31, wherein the membrane structure
2 further comprising an insulative diaphragm stacked over
3 the upper electrode and anchored to the base around an
4 edge of the insulative diaphragm.

5
1 33. The sensor of claim 30, wherein the upper electrode
2 comprises a conductive membrane having an annular crease.

3
1 34. The sensor of claim 30, wherein said each membrane switch
2 defines a closed chamber defined generally between the
3 lower electrode and the membrane structure, the chamber
4 being substantially closed to external particles so as to
5 protect the lower electrode and the upper electrode from
6 contamination.

1 35. The sensor of claim 34, wherein the closed chamber is
2 open to a passage of air from an external environment
3 of the sensor, for allowing an equalization of pressure
4 between the external environment and the closed
5 chamber.

6
1 36. The sensor of claim 34, further comprising a set of
2 interswitch tunnels establishing fluidic communication
3 between a plurality of closed chambers of adjacent
4 switches, for allowing an equalization of pressure
5 between the plurality of closed chambers.

6
1 37. The sensor of claim 30, wherein the texture is a skin
2 texture, and the array of membrane switches are spaced to
3 sense the skin texture.

4
1 38. The sensor of claim 37, wherein an interswitch spacing
2 of the array is less than or equal to 400 microns.

3
1 39. The sensor of claim 38, wherein the interswitch
2 spacing is less than or equal to 200 microns.

3
1 40. An integrated circuit chip sensor for sensing a texture that
2 has a plurality of ridges and a plurality of valleys,
3 comprising:

- 4 a) a substrate;
5 b) a plurality of row lines;
6 c) a plurality of column lines; and
7 d) a plurality of membrane switches disposed on the
8 substrate in an array such that each row line and each
9 column line is connected to a plurality of membrane
10 switches, each switch including:
11 a lower electrode electrically connected to one of the
12 row lines; and

13 a flexible membrane comprising an upper electrode
14 spaced apart from said lower electrode when in a
15 quiescent state and electrically connected to one
16 of the column lines; wherein

17 a ridge of the texture causes flexure of the
18 membrane and thereby results in movement of
19 the upper electrode and a change in a state
20 of electrical contact between the upper
21 electrode and the lower electrode, and
22 wherein

23 a valley of the texture disposed over another of
24 the switches does not result in flexure of
25 the membrane and the change in state of
26 electrical contact between the upper
27 electrode and the lower electrode associated
28 with said another switch.
29

1 41. The sensor of claim 40, wherein the membrane structure
2 further comprises an insulative diaphragm stacked over
3 the upper electrode.
4

1 42. The sensor of claim 41, wherein a height of a top
2 surface of the insulative diaphragm is within 4 μm
3 of a top height of a support surface of the sensor,
4 the support surface being outside of any membrane
5 structure of the array.
6

1 43. The sensor of claim 40, wherein said each membrane switch
2 defines a closed chamber defined generally between the
3 lower electrode and the membrane structure, the chamber
4 being substantially closed to external particles so as to
5 protect the lower electrode and the upper electrode from
6 contamination.

7
1 44. The sensor of claim 43, wherein the closed chamber is
2 open to a passage of air from an external environment
3 of the sensor, for allowing an equalization of pressure
4 between the external environment and the closed
5 chamber.

6
1 45. The sensor of claim 43, wherein said each membrane
2 switch includes a set of sealed vents extending between
3 the chamber and an exterior of the chamber, wherein the
4 set of vents in an unsealed state provide access to the
5 chamber for removing a sacrificial material from the
6 chamber during a manufacture of the sensor.

7
1 46. The sensor of claim 43, further comprising a set of
2 interswitch tunnels establishing fluidic communication
3 between a plurality of closed chambers of adjacent
4 switches, for allowing an equalization of pressure
5 between the plurality of closed chambers.

6
1 47. The sensor of claim 40 wherein the array of membrane
2 switches is disposed on the substrate such that a
3 spacing between adjacent switches in the array is less
4 than one half of a spacing between adjacent ridges.
5

1 48. A texture sensor for sensing a texture having a plurality of
2 protrusions and a plurality of valleys, the sensor
3 comprising an array of membrane switches disposed on a base,
4 each membrane switch comprising:

- 5 a) a fixed electrode rigidly coupled to the base; and
6 b) a flexible upper membrane structure disposed over the
7 base such that a cavity separates a central region of

the membrane structure and the base when the fixed electrode and the movable electrode are not in contact, the membrane structure comprising a movable electrode disposed facing the fixed electrode, wherein disposing a protrusion of the texture over said each membrane switch causes a flexure of the membrane resulting in a change in contact state between the fixed electrode and the movable electrode, and wherein disposing a valley of the texture over said each membrane switch does not result in the change in contact state between the fixed electrode and the movable electrode.

49. The sensor of claim 48, wherein the fixed electrode is disposed underneath the movable electrode, and wherein the change in contact state is a change from an open quiescent state to a closed state.

50. The sensor of claim 48, wherein the fixed electrode is disposed above the movable electrode, and wherein the change in contact state is a change from a closed quiescent state to an open state.

51. A method of detecting a texture, comprising:

- a) depressing the texture over a sensor comprising an array of membrane switches, each membrane switch comprising a fixed lower electrode and a flexible upper membrane structure including an upper electrode disposed over the lower electrode;
- b) identifying a plurality of closed membrane switches, wherein a ridge of the texture disposed over each of the closed switches causes a flexure of a membrane structure of said each of the closed switches and an

11 electrical contact between a lower electrode and an
12 upper electrode of said each of the closed switches;
13 and

- 14 c) identifying a plurality of open membrane switches,
15 wherein a valley of the texture disposed over each of
16 the open switches does not cause an electrical contact
17 between a lower electrode and an upper electrode of
18 said each of the open switches.

19
1 52. The method of claim 51, wherein the texture is a skin
2 texture.

3
1 53. The method of claim 52, wherein the skin texture is a
2 fingerprint texture.

3
1 54. The method of claim 51, further comprising a step of
2 equalizing a plurality of pressures corresponding to a
3 plurality of interconnected closed chambers defined by
4 adjacent membrane switches of the array.

5
1 55. The method of claim 51, further comprising a step of
2 determining a quiescent state of said each membrane
3 switch while the texture is not depressed over the
4 sensor.

5
1 56. The method of claim 54, wherein identifying the
2 plurality of closed membrane switches comprises
3 identifying a subset of membrane switches having
4 undergone a change in state between a time of
5 determining the quiescent state and a time of
6 depressing the texture over the sensor.

1 57. A method of making an integrated texture sensor for sensing
2 a texture that is protected from external contaminating
3 particulates and will self-equalize using air from outside
4 the sensor, comprising:

- 5 a) forming a plurality of row lines and a plurality of
6 column lines on a substrate, each of the row lines and
7 column lines being insulated from each other, the row
8 lines and column lines intersecting to form a switch
9 area between adjacent row lines and adjacent column
10 lines;
11 b) forming a lower electrode in each of a plurality of
12 switch areas;
13 c) forming a sacrificial area directly over the lower
14 electrode and a non-sacrificial area around the
15 sacrificial area;
16 d) forming a membrane above the sacrificial area, the
17 membrane being anchored to the non-sacrificial area,
18 the membrane comprising an upper electrode disposed
19 directly above the sacrificial area, wherein the
20 membrane does not cover a channel area adjacent to the
21 sacrificial area;
22 e) removing the sacrificial area by introducing a
23 sacrificial etchant through the channel area, thereby
24 forming a cavity region at each sacrificial area; and
25 f) sealing the channel so as to close the cavity region
26 from the external contaminating particulates while
27 still self-equalizing pressure using the air that is
28 external to the sensor that can flow through the
29 channel.
30

1 58. A method of making a skin-texture sensor for sensing a skin
2 texture having a plurality of ridges and a plurality of
3 valleys, comprising:

- 4 a) establishing a base;

- 5 b) disposing a plurality of conductive row lines on the
6 base;
- 7 c) disposing a plurality of conductive column lines on the
8 base, the column lines being insulated from the row
9 lines; and
- 10 d) forming an array of membrane switches on the base such
11 that a spacing between adjacent switches in the array
12 is less than one half of a spacing between adjacent
13 ridges, each membrane switch corresponding to a pair of
14 one of the row lines and one of the column lines,
15 wherein forming the array comprises:
16 disposing a lower electrode on the base,
17 electrically connecting the lower electrode to said one
18 of the row lines,
19 disposing a flexible upper membrane structure over the
20 lower electrode, the membrane structure comprising
21 an upper electrode disposed facing the lower
22 electrode and connected to said one of the column
23 lines, wherein
24 applying a ridge of the texture to said each membrane
25 switch causes a flexure of the membrane resulting
26 in a contact between the lower electrode and the
27 upper electrode, the contact establishing an
28 electrical communication between said one of the
29 row lines and said one of the column lines, and
30 wherein
31 disposing a valley of the texture over said each
32 membrane switch does not result in the contact
33 between the lower electrode and the upper
34 electrode.
- 35